

2SD1527

Silicon NPN Triple Diffused

RENESAS

ADE-208-913 (Z)

1st. Edition

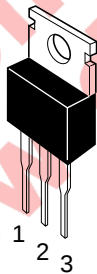
September 2000

Application

High voltage power amplifier

Outline

TO-220AB



- 1. Base
- 2. Collector (Flange)
- 3. Emitter

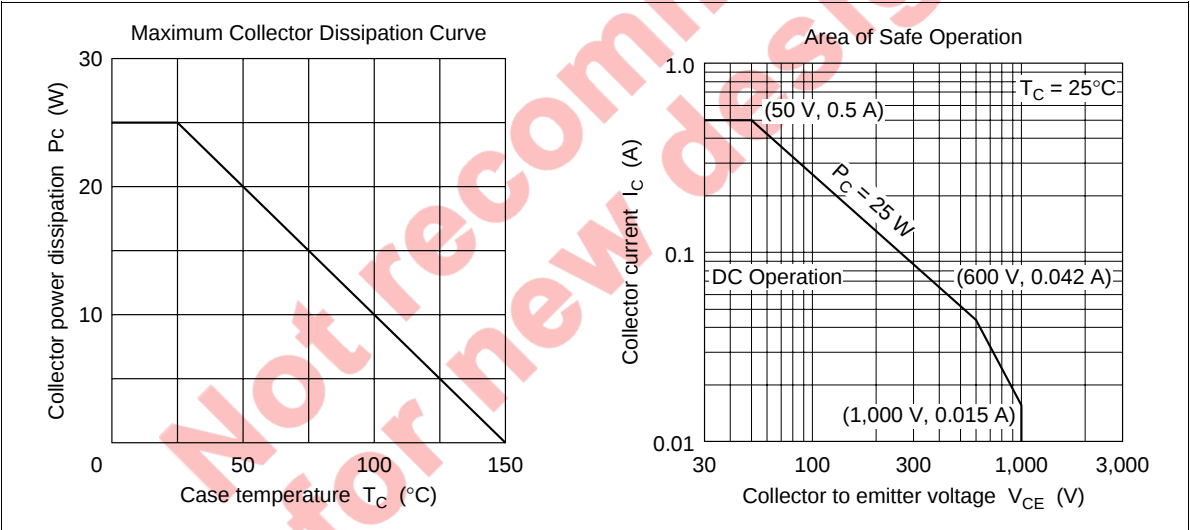
Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	1000	V
Collector to emitter voltage	V_{CEO}	1000	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	0.5	A
Collector power dissipation	P_C	1.8	W
	P_C^{*1}	25	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

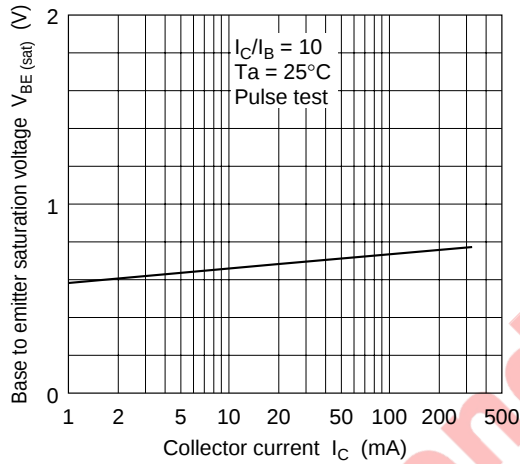
Note: 1. Value at $T_c = 25^{\circ}\text{C}$.

Electrical Characteristics (Ta = 25°C)

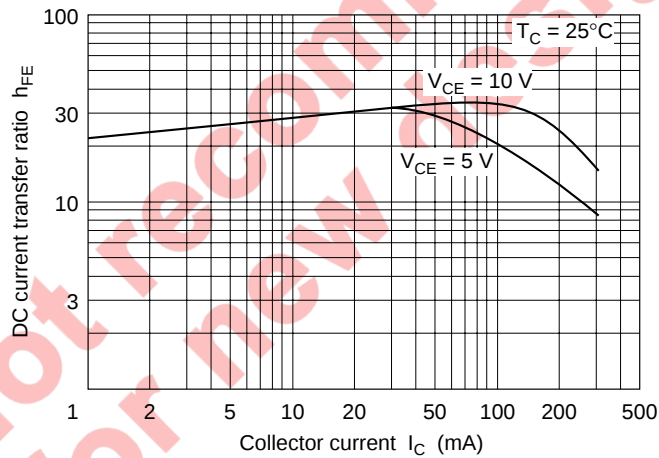
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	1000	—	—	V	$I_C = 1\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 1\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 800\text{ V}$, $I_E = 0$
DC current transfer ratio	h_{FE1}	10	—	—		$V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$
	h_{FE2}	10	—	—		$V_{CE} = 5\text{ V}$, $I_C = 100\text{ mA}$
Base to emitter voltage	V_{BE}	—	—	1.2	V	$V_{CE} = 5\text{ V}$, $I_C = 100\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5	V	$I_C = 300\text{ mA}$, $I_B = 60\text{ mA}$
Gain bandwidth product	f_T	—	5	—	MHz	$V_{CE} = 20\text{ V}$, $I_C = 50\text{ mA}$
Collector output capacitance	C_{ob}	—	5	—	pF	$V_{CB} = 100\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$



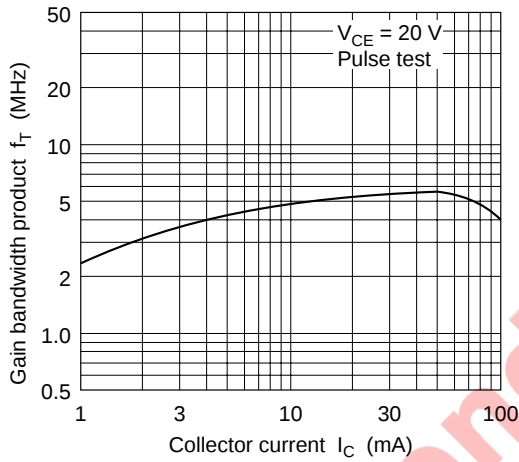
Base to Emitter Saturation Voltage
vs. Collector Current



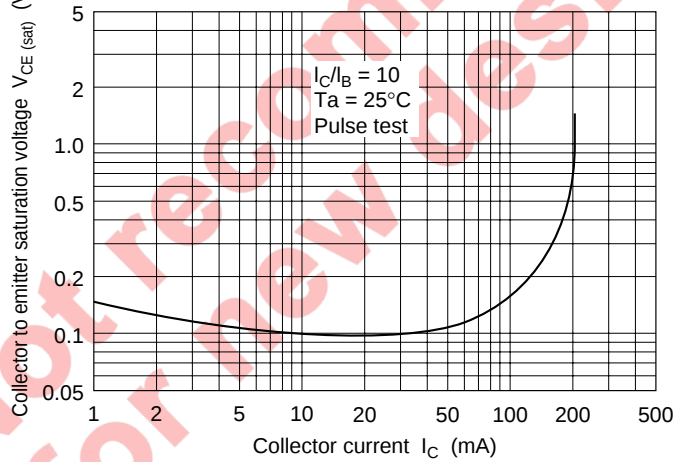
DC Current Transfer Ratio
vs. Collector Current



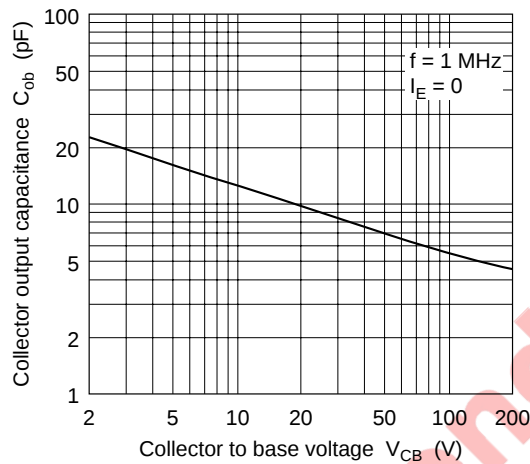
Gain Bandwidth Product
vs. Collector Current



Collector to Emitter Saturation Voltage
vs. Collector Current



Collector Output Capacitance
vs. Collector to Base Voltage



Not recommended
for new design